- S51: (165) S50 near2 S41
- S52: (60) S46 and S51
- S53: (40) S52 and S47
- S54: (2) S52 and S45
- S55: (71) S53 S54 S49
- S56: (810454) nm nanometer nano adj meter angstrom ang
- S57: (56) S55 and S56
- S58: (1713967) etch$4 stop
- S59: (33033) S58 with S56
- S60: (33) S57 and S59
- S61: (11) S60 and S45
- S62: (11) S54 S61
- S63: (11) S62 and S56
- S64: (0) 10/800510
- S65: (1355810) organic sic sicn sico
- S66: (490) S41 near9 S65
- S67: (15) S51 and S66
- S68: (26) S63 S67
- Favorites
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	U	1	Inventor	Document	Issue	P	Title	Curren	Current X	Retrieva	S	C	P	2	3	4	5	Image	Do	P
1			Ruelke, Ha	US 200400	2004	1	Barrier layer for a copper metallization	257/77	257/751;									US 20040		
2			Cho; Jaesh	US 570790	1998	7	Method utilizing an etch stop layer	438/59	257/E21.2									US 57079		
3			Morrow, Xi	US 200400	2004	1	Method and apparatus for forming met	438/69										US 20040		
4			Engelmann	US 200500	2005	1	Metal line having an increased resista	257/76	257/751;									US 20050		
5			Morrow, Xi	US 200402	2004	1	Method and apparatus for forming met	438/68										US 20040		
6			Wang, Pin-	US 200401	2004	8	METHOD FOR MANUFACTURING A S	438/62	257/E21.5									US 20040		
7			Chen, Tze-	US 200401	2004	1	Bilayer HDP CVD / PE CVD cap in adv	257/75	257/750									US 20040		
8			Kusumi, Yo	US 200401	2004	9	Method of manufacturing electronic de	438/59										US 20040		
9			Chen, Tze-	US 200401	2004	1	Bilayer HDP CVD/PE CVD cap in adva	438/20										US 20040		
10			Maiz, Jose	US 200400	2004	1	A METHOD OF FORMING SURFACE A	257/77	257/E23.1									US 20040		